



STPS10L40CT/CG/CF

LOW DROP POWER SCHOTTKY RECTIFIER

MAJOR PRODUCTS CHARACTERISTICS

I _{F(AV)}	2x5 A
V _{RRM}	40 V
T _{j(max)}	150°C
V _{F(max)}	0.46 V

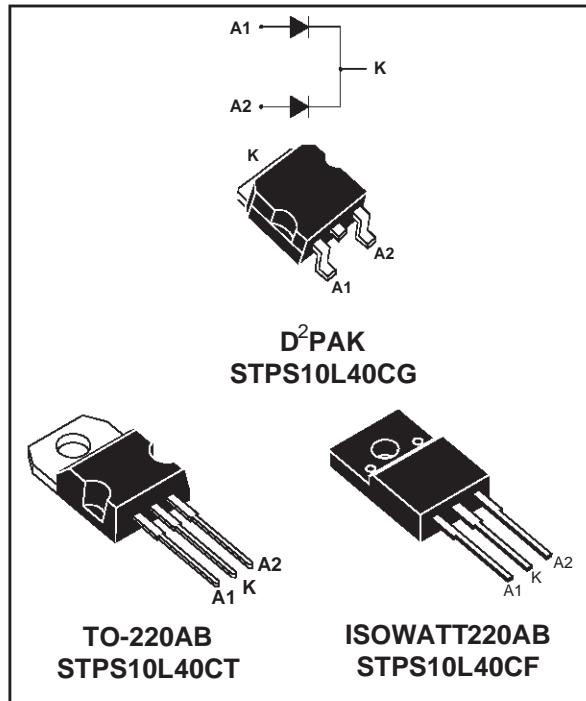
FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP MEANING VERY SMALL CONDUCTION LOSSES
- LOW DYNAMIC LOSSES AS A RESULT OF THE SCHOTTKY BARRIER
- AVALANCHE RATED

DESCRIPTION

Dual center tap Schottky rectifiers suited for switchmode power supply and high frequency DC to DC converters.

Packaged in TO-220AB, ISOWATT220AB and D²PAK, these devices are intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit		
V _{RRM}	Repetitive peak reverse voltage			40	V		
I _{F(RMS)}	RMS forward current			20	A		
I _{F(AV)}	Average forward current	T _c = 135°C $\delta = 0.5$	Per diode Per device	5 10	A		
I _{FSM}	Surge non repetitive forward current	tp = 10 ms Sinusoidal		150	A		
I _{RRM}	Peak repetitive reverse current	tp = 2 μs F = 1kHz square		1	A		
I _{RSR}	Non repetitive peak reverse current	tp = 100 μs square		2	A		
T _{stg}	Storage temperature range			-65 to +150	°C		
T _j	Maximum operating junction temperature *			150	°C		
dV/dt	Critical rate of rise of reverse voltage			10000	V/μs		

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

STPS10L40CT/CG/CF

THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AB D ² PAK	Per diode Total	3 1.7	$^{\circ}\text{C/W}$
$R_{th(c)}$			Coupling	0.35	
$R_{th(j-c)}$	Junction to case	ISOWATT220AB	Per diode Total	5 3.8	$^{\circ}\text{C/W}$
$R_{th(c)}$			Coupling	2.5	

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R *	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			0.2	mA
		$T_j = 100^{\circ}\text{C}$			8	25	mA
V_F *	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 5 \text{ A}$			0.53	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 5 \text{ A}$		0.36	0.46	
		$T_j = 25^{\circ}\text{C}$	$I_F = 10 \text{ A}$			0.67	
		$T_j = 125^{\circ}\text{C}$	$I_F = 10 \text{ A}$		0.49	0.59	

Pulse test : * $t_p = 380 \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.33 \times I_{F(AV)} + 0.026 I_{F}^2(\text{RMS})$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

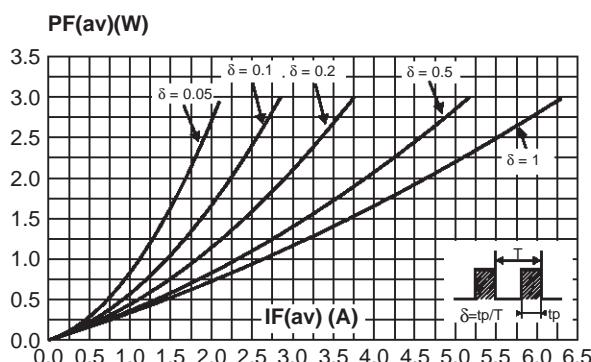


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$, per diode).

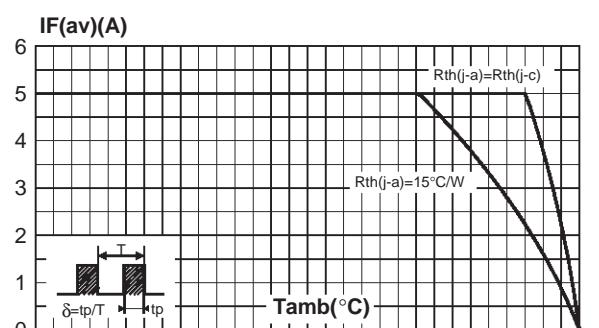


Fig. 3-1: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (TO-220AB and D²PAK).

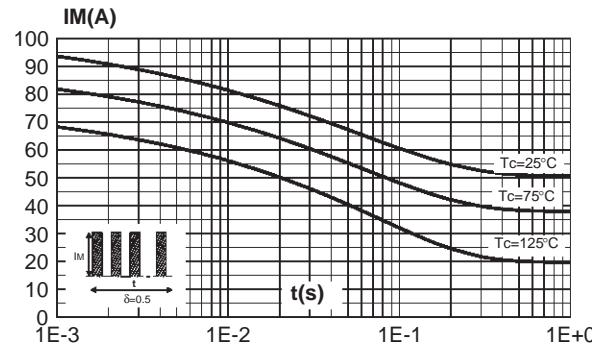


Fig. 4-1: Relative variation of thermal impedance junction to case versus pulse duration. (TO-220AB and D²PAK).

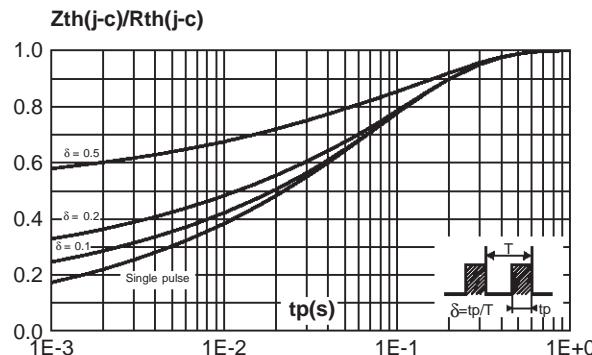


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

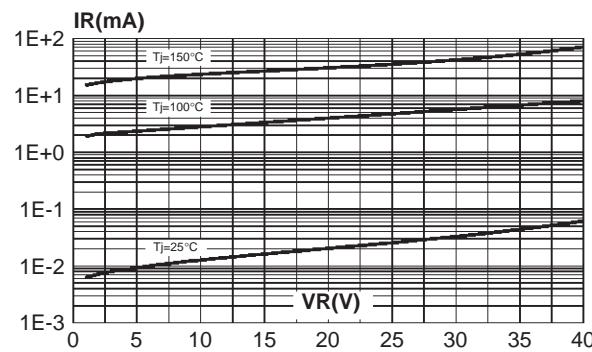


Fig. 3-2: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (ISOWATT220AB).

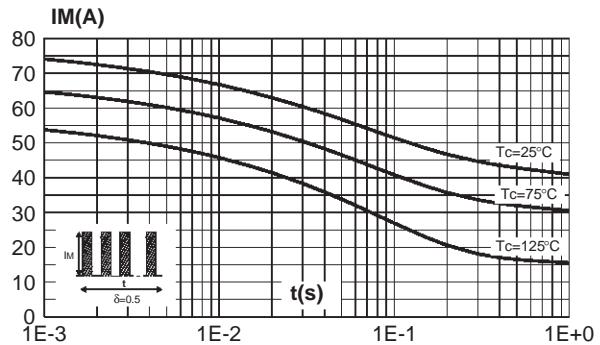


Fig. 4-2: Relative variation of thermal impedance junction to case versus pulse duration. (ISOWATT220AB).

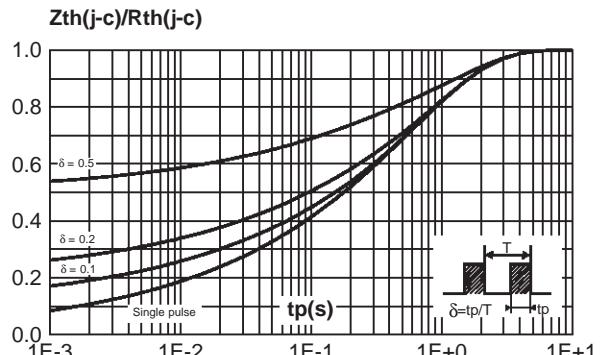
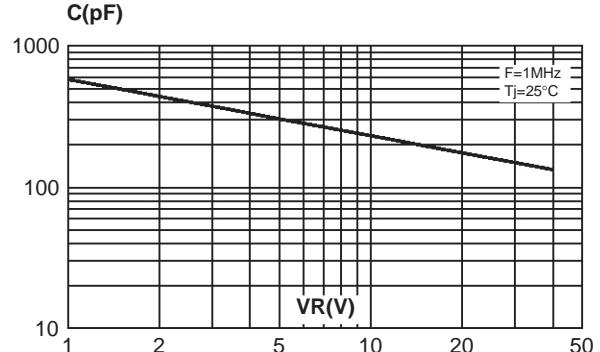


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).



STPS10L40CT/CG/CF

Fig. 7: Forward voltage drop versus forward current (maximum values, per diode).

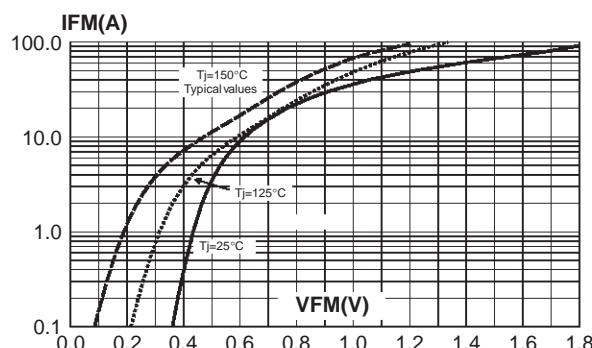
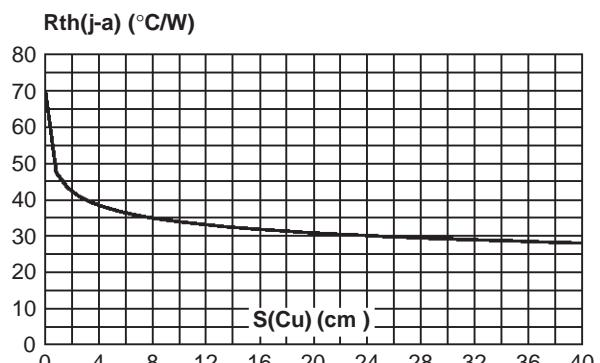
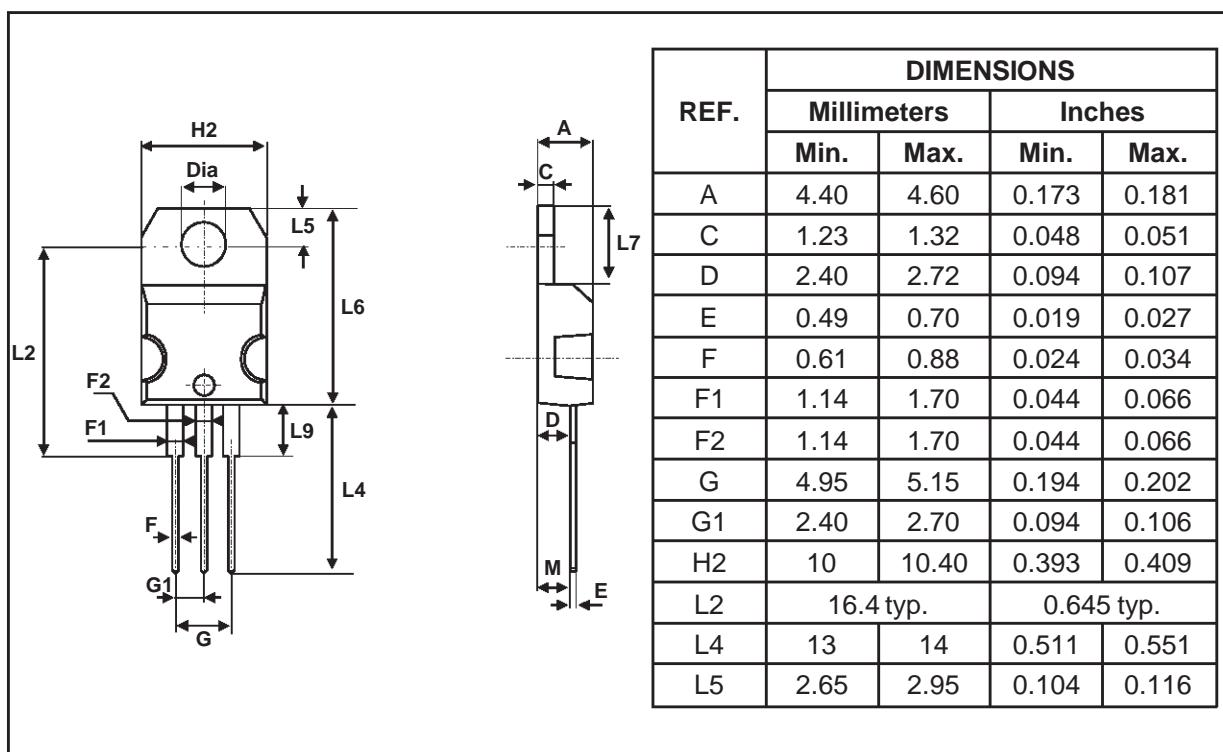


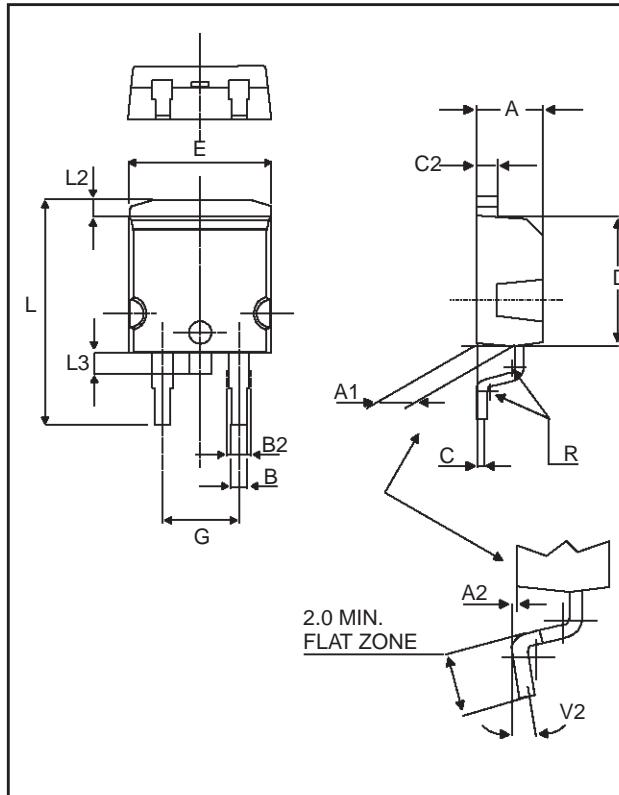
Fig. 8: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35 μ m)(D²PAK).



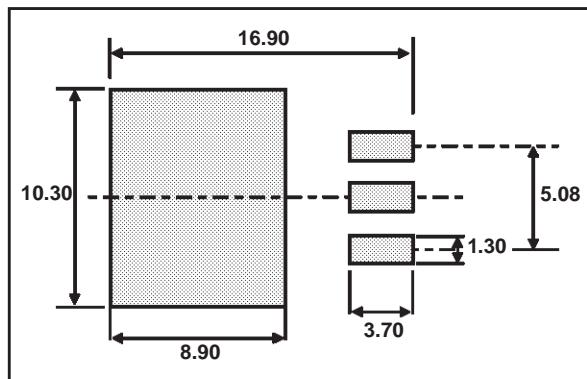
PACKAGE MECHANICAL DATA TO-220AB



- Cooling method : C
- Recommended torque value : 0.55 m.N
- Maximum torque value : 0.70 m.N

PACKAGE MECHANICAL DATA
D²PAK


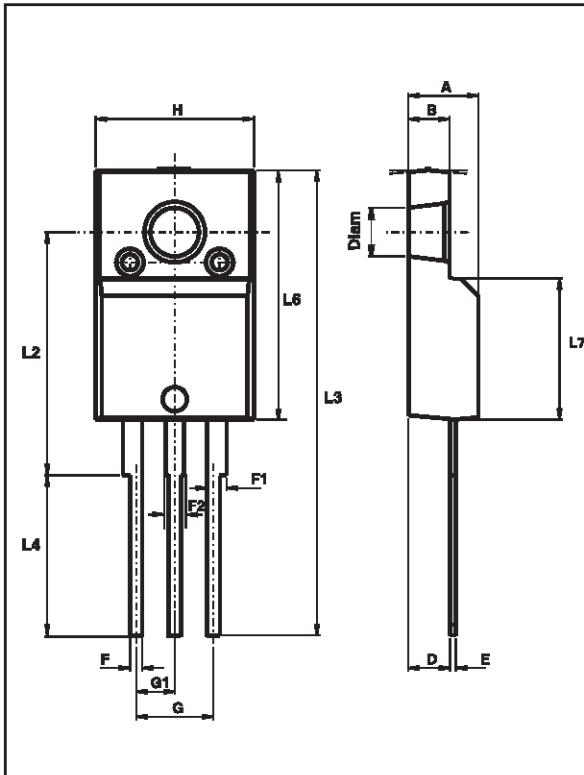
REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.70		0.93	0.027		0.037
B2	1.25	1.40		0.049	0.055	
C	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	8.95		9.35	0.352		0.368
E	10.00		10.28	0.393		0.405
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.40	0.050		0.055

FOOT PRINT DIMENSIONS (in millimeters)


- Cooling method: by conduction (method C)

STPS10L40CT/CG/CF

PACKAGE MECHANICAL DATA ISOWATT220AB



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	2.50		2.70	0.098		0.106
D	2.50		2.75	0.098		0.108
E	0.40		0.70	0.016		0.028
F	0.75		1.00	0.030		0.039
F1	1.15		1.70	0.045		0.067
F2	1.15		1.70	0.045		0.067
G	4.95		5.20	0.195		0.205
G1	2.40		2.70	0.094		0.106
H	10.00		10.40	0.394		0.409
L2		16.00			0.630	
L3	28.60		30.60	1.125		1.205

- Cooling method : C
- Recommended torque value : 0.55m.N
- Maximum torque value : 0.70m.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS10L40CT	STPS10L40CT	TO-220AB	2.23g	50	Tube
STPS10L40CG	STPS10L40CG	D ² PAK	1.48g	50	Tube
STPS10L40CG-TR	STPS10L40CG	D ² PAK	1.48g	500	Tape & reel
STPS10L40CF	STPS10L40CF	ISOWATT220AB	2.08g	50	Tube

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